

# Schottky barrier diode

## RB520S-30

### ● Applications

Low current rectification and high speed switching

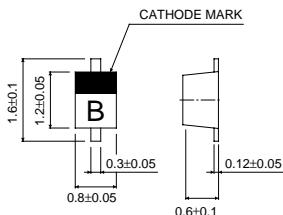
### ● Features

- 1) Extremely small surface mounting type. (EMD2)
- 2) Low  $I_R$ . ( $I_R=0.1\mu A$  Typ.)
- 3) High reliability.

### ● Construction

Silicon epitaxial planar

### ● External dimensions (Units : mm)



ROHM : EMD2

EIAJ : SC-79

JEDEC : SOD-523

### ● Absolute maximum ratings ( $T_a=25^\circ C$ )

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	30	V
Mean rectifying current	$I_o$	200	mA
Peak forward surge current*	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	$^\circ C$
Storage temperature	$T_{stg}$	-40~+125	$^\circ C$

\* 60Hz for 1  $\text{AC} \sim$

### ● Electrical characteristics ( $T_a=25^\circ C$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	—	—	0.60	V	$I_F = 200\text{mA}$
Reverse current	$I_R$	—	—	1.0	$\mu\text{A}$	$V_R = 10\text{V}$

Note) ESD sensitive product handling required.

## Diodes

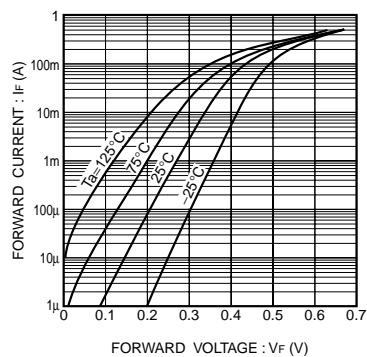
**●Electrical characteristic curves ( $T_a=25^\circ\text{C}$ )**

Fig. 1 Forward characteristics

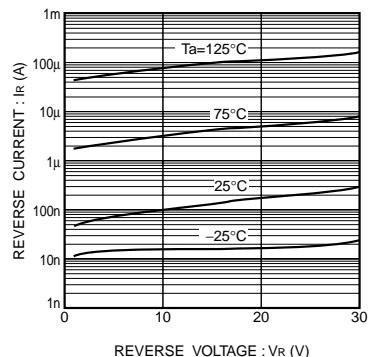


Fig. 2 Reverse characteristics

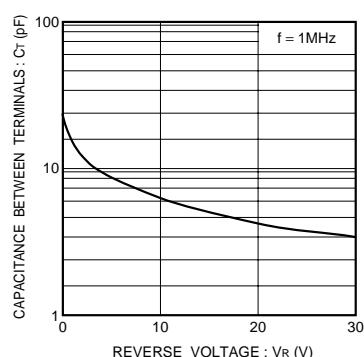
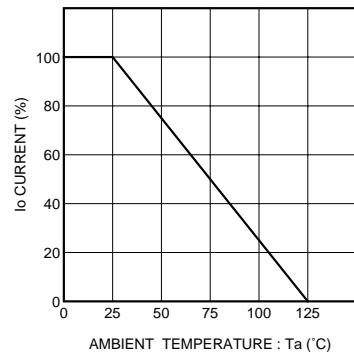


Fig. 3 Capacitance between terminals characteristics

Fig. 4. Derating curve  
(mounting on glass epoxy PCBs)